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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, SPI, UART/USART
Peripherals	DMA, I ² S, LVD, POR, PWM, WDT
Number of I/O	70
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 37x16b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mk10dx128vll7

3.1.1 Example

This is an example of an operating requirement, which you must meet for the accompanying operating behaviors to be guaranteed:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	0.9	1.1	V

3.2 Definition: Operating behavior

An *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

3.2.1 Example

This is an example of an operating behavior, which is guaranteed if you meet the accompanying operating requirements:

Symbol	Description	Min.	Max.	Unit
I _{WP}	Digital I/O weak pullup/pulldown current	10	130	μA

3.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

3.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

3.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

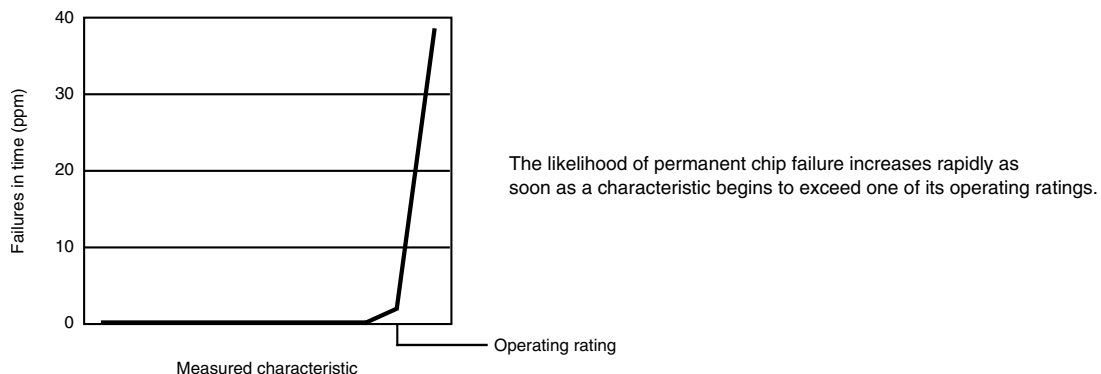
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

3.4.1 Example

This is an example of an operating rating:

Symbol	Description	Min.	Max.	Unit
V _{DD}	1.0 V core supply voltage	−0.3	1.2	V

3.5 Result of exceeding a rating



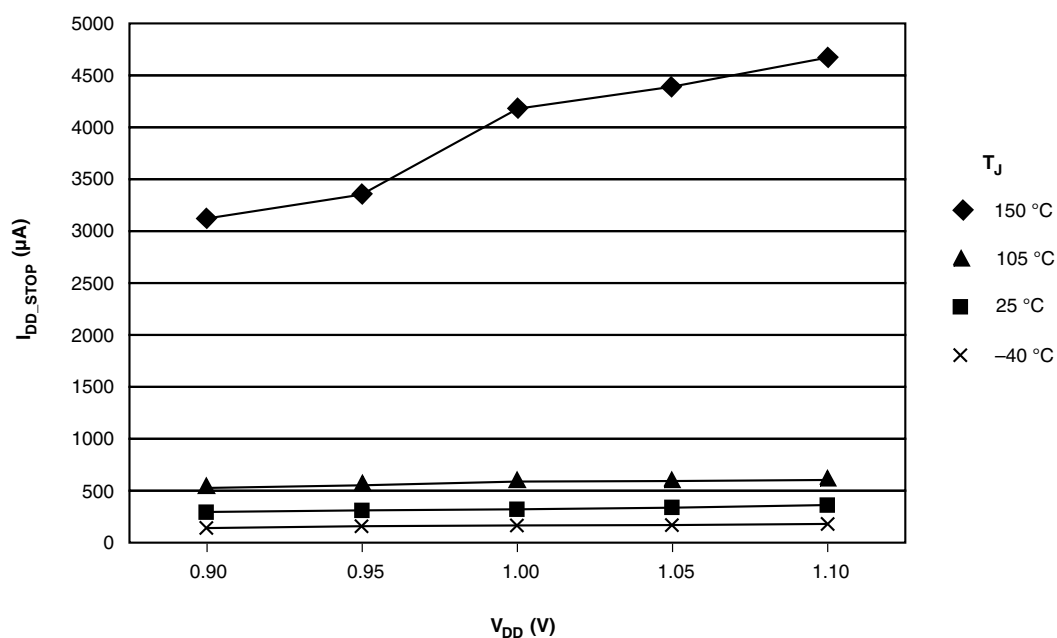
3.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	μA

3.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



3.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

Symbol	Description	Min.	Max.	Unit
I_{DD}	Digital supply current	—	185	mA
V_{DIO}	Digital input voltage (except $\overline{RESET}$, EXTAL, and XTAL)	-0.3	5.5	V
V_{AIO}	Analog ¹ , $\overline{RESET}$, EXTAL, and XTAL input voltage	-0.3	$V_{DD} + 0.3$	V
I_D	Maximum current single pin limit (applies to all digital pins)	-25	25	mA
V_{DDA}	Analog supply voltage	$V_{DD} - 0.3$	$V_{DD} + 0.3$	V
V_{BAT}	RTC battery supply voltage	-0.3	3.8	V

1. Analog pins are defined as pins that do not have an associated general purpose I/O port function.

5 General

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

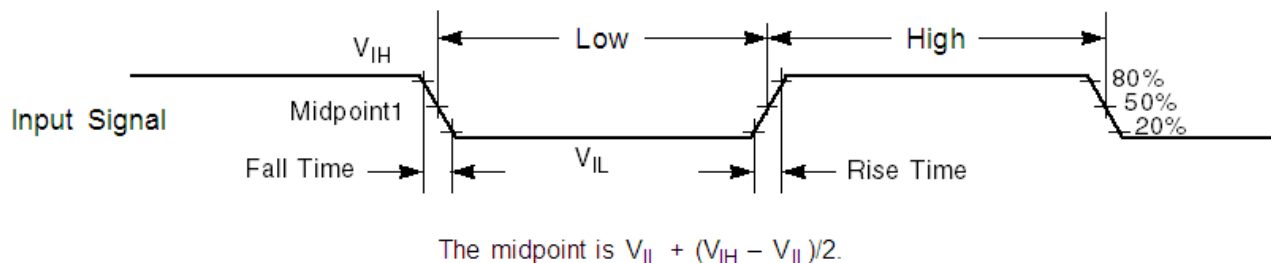


Figure 1. Input signal measurement reference

All digital I/O switching characteristics assume:

- output pins
 - have $C_L=30\text{pF}$ loads,
 - are configured for fast slew rate ($\text{PORTx_PCRn[SRE]}=0$), and
 - are configured for high drive strength ($\text{PORTx_PCRn[DSE]}=1$)
- input pins
 - have their passive filter disabled ($\text{PORTx_PCRn[PFE]}=0$)

5.2 Nonswitching electrical specifications

5.2.1 Voltage and current operating requirements

Table 1. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	
$V_{DD} - V_{DDA}$	V_{DD} -to- V_{DDA} differential voltage	-0.1	0.1	V	
$V_{SS} - V_{SSA}$	V_{SS} -to- V_{SSA} differential voltage	-0.1	0.1	V	
V_{BAT}	RTC battery supply voltage	1.71	3.6	V	
V_{IH}	Input high voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	$0.7 \times V_{DD}$ $0.75 \times V_{DD}$	— —	V V	
V_{IL}	Input low voltage $2.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ $1.7\text{ V} \leq V_{DD} \leq 2.7\text{ V}$	— —	$0.35 \times V_{DD}$ $0.3 \times V_{DD}$	V V	
V_{HYS}	Input hysteresis	$0.06 \times V_{DD}$	—	V	
I_{ICDIO}	Digital pin negative DC injection current — single pin $V_{IN} < V_{SS}-0.3\text{V}$	-5	—	mA	1
I_{ICAIO}	Analog ² , EXTAL, and XTAL pin DC injection current — single pin $V_{IN} < V_{SS}-0.3\text{V}$ (Negative current injection) $V_{IN} > V_{DD}+0.3\text{V}$ (Positive current injection)	-5 —	— +5	mA	3
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins - Negative current injection - Positive current injection	-25 —	— +25	mA	
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	
V_{RFVBAT}	V_{BAT} voltage required to retain the VBAT register file	V_{POR_VBAT}	—	V	

1. All 5 V tolerant digital I/O pins are internally clamped to V_{SS} through a ESD protection diode. There is no diode connection to V_{DD} . If V_{IN} greater than V_{DIO_MIN} ($=V_{SS}-0.3\text{V}$) is observed, then there is no need to provide current limiting resistors at the pads. If this limit cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{DIO_MIN}-V_{IN})/|I_{IC}|$.
2. Analog pins are defined as pins that do not have an associated general purpose I/O port function.
3. All analog pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{AIO_MIN} ($=V_{SS}-0.3\text{V}$) and V_{IN} is less than V_{AIO_MAX} ($=V_{DD}+0.3\text{V}$) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as $R=(V_{AIO_MIN}-V_{IN})/|I_{IC}|$. The positive injection current limiting resistor is calculated as $R=(V_{IN}-V_{AIO_MAX})/|I_{IC}|$. Select the larger of these two calculated resistances.

5.2.2 LVD and POR operating requirements

Table 2. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR}	Falling VDD POR detect voltage	0.8	1.1	1.5	V	
V _{LVDH}	Falling low-voltage detect threshold — high range (LVDV=01)	2.48	2.56	2.64	V	
V _{LVW1H}	Low-voltage warning thresholds — high range					1
	• Level 1 falling (LVWV=00)	2.62	2.70	2.78	V	
V _{LVW2H}	• Level 2 falling (LVWV=01)	2.72	2.80	2.88	V	
V _{LVW3H}	• Level 3 falling (LVWV=10)	2.82	2.90	2.98	V	
V _{LVW4H}	• Level 4 falling (LVWV=11)	2.92	3.00	3.08	V	
V _{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±80	—	mV	
V _{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	
V _{LVW1L}	Low-voltage warning thresholds — low range					1
	• Level 1 falling (LVWV=00)	1.74	1.80	1.86	V	
V _{LVW2L}	• Level 2 falling (LVWV=01)	1.84	1.90	1.96	V	
V _{LVW3L}	• Level 3 falling (LVWV=10)	1.94	2.00	2.06	V	
V _{LVW4L}	• Level 4 falling (LVWV=11)	2.04	2.10	2.16	V	
V _{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±60	—	mV	
V _{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	
t _{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	μs	

1. Rising thresholds are falling threshold + hysteresis voltage

Table 3. VBAT power operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V _{POR_VBAT}	Falling VBAT supply POR detect voltage	0.8	1.1	1.5	V	

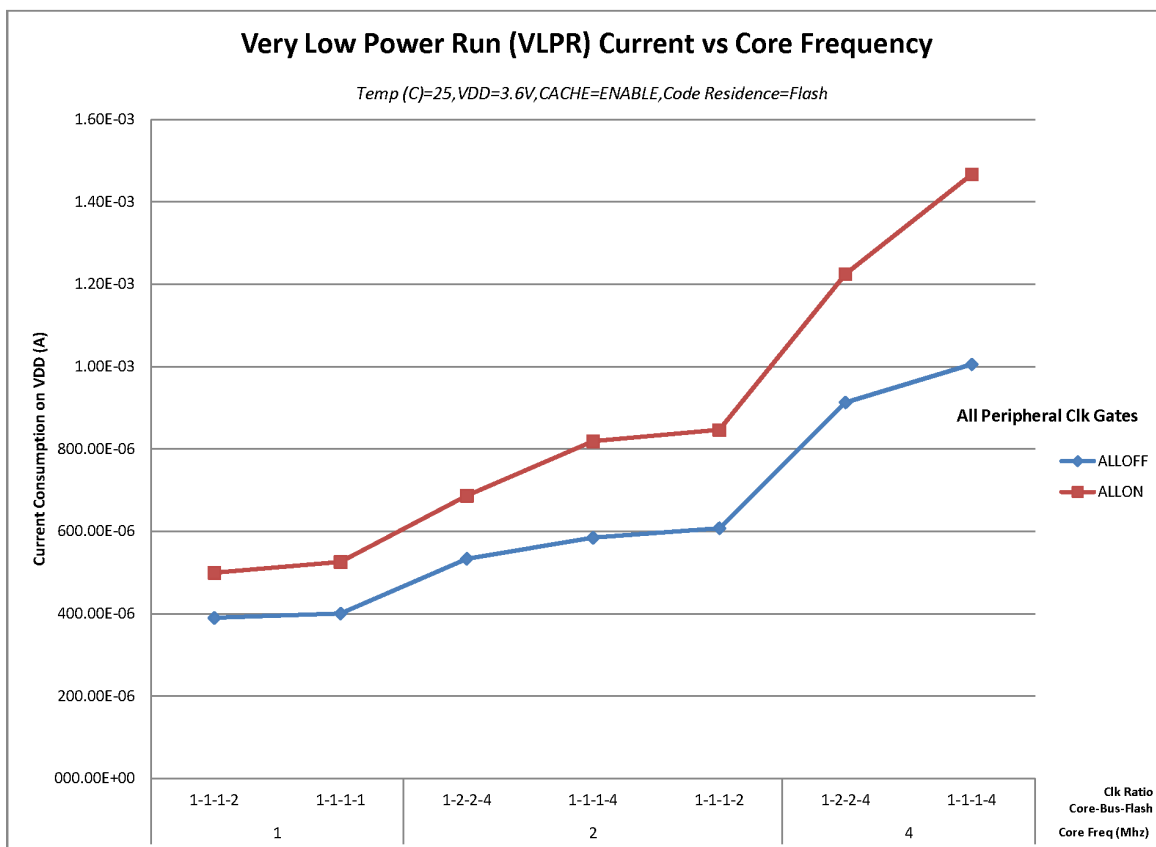


Figure 3. VLPR mode supply current vs. core frequency

5.2.6 Designing with radiated emissions in mind

To find application notes that provide guidance on designing your system to minimize interference from radiated emissions:

1. Go to www.freescale.com.
2. Perform a keyword search for “EMC design.”

5.2.7 Capacitance attributes

Table 7. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C _{IN_A}	Input capacitance: analog pins	—	7	pF
C _{IN_D}	Input capacitance: digital pins	—	7	pF

Table 9. General switching specifications (continued)

Symbol	Description	Min.	Max.	Unit	Notes
	GPIO pin interrupt pulse width (digital glitch filter disabled, analog filter disabled) — Asynchronous path	16	—	ns	3
	External reset pulse width (digital glitch filter disabled)	100	—	ns	3
	Mode select (EZP_CS) hold time after reset deassertion	2	—	Bus clock cycles	
	Port rise and fall time (high drive strength) - Slew disabled $1.71 \leq V_{DD} \leq 2.7V$ $2.7 \leq V_{DD} \leq 3.6V$ - Slew enabled $1.71 \leq V_{DD} \leq 2.7V$ $2.7 \leq V_{DD} \leq 3.6V$	— — — —	12 6 36 24	ns ns ns ns	4
	Port rise and fall time (low drive strength) - Slew disabled $1.71 \leq V_{DD} \leq 2.7V$ $2.7 \leq V_{DD} \leq 3.6V$ - Slew enabled $1.71 \leq V_{DD} \leq 2.7V$ $2.7 \leq V_{DD} \leq 3.6V$	— — — —	12 6 36 24	ns ns ns ns	5

1. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In Stop, VLPS, LLS, and VLLSx modes, the synchronizer is bypassed so shorter pulses can be recognized in that case.
2. The greater synchronous and asynchronous timing must be met.
3. This is the minimum pulse width that is guaranteed to be recognized as a pin interrupt request in Stop, VLPS, LLS, and VLLSx modes.
4. 75pF load
5. 15pF load

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 10. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	−40	125	°C
T_A	Ambient temperature	−40	105	°C

6.1.2 JTAG electricals

Table 12. JTAG limited voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	3.6	V
J1	TCLK frequency of operation - Boundary Scan - JTAG and CJTAG - Serial Wire Debug	0 0 0	10 25 50	MHz
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width - Boundary Scan - JTAG and CJTAG - Serial Wire Debug	50 20 10	— — —	ns ns ns
J4	TCLK rise and fall times	—	3	ns
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1	—	ns
J11	TCLK low to TDO data valid	—	17	ns
J12	TCLK low to TDO high-Z	—	17	ns
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8	—	ns

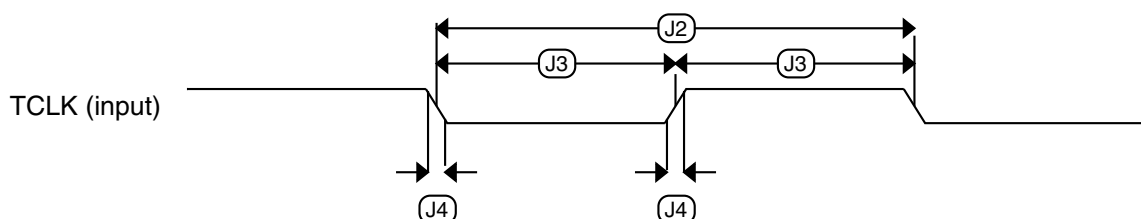
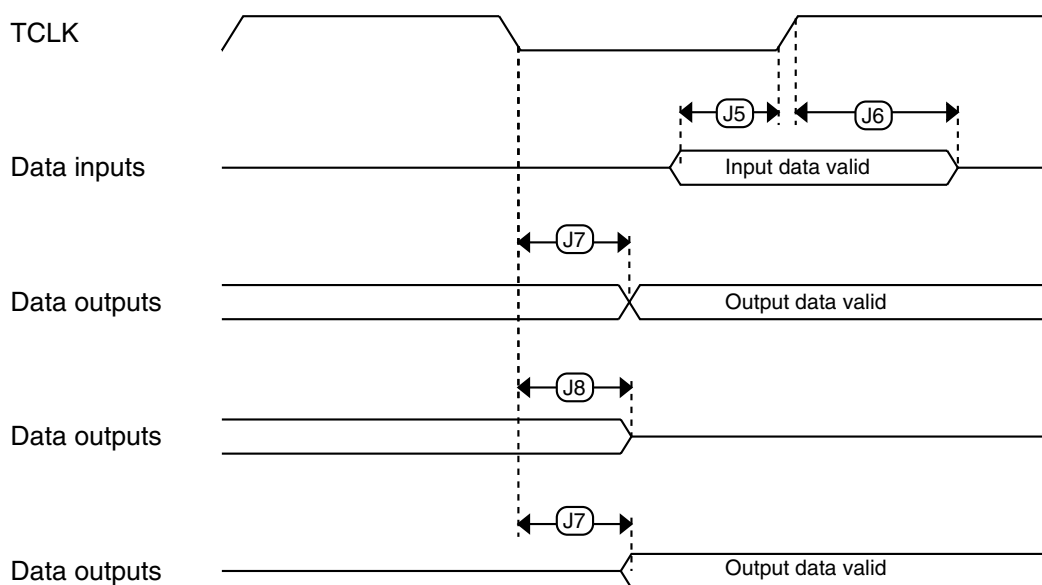
Table 13. JTAG full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	TCLK frequency of operation - Boundary Scan - JTAG and CJTAG - Serial Wire Debug	0 0 0	10 20 40	MHz
J2	TCLK cycle period	1/J1	—	ns
J3	TCLK clock pulse width - Boundary Scan - JTAG and CJTAG - Serial Wire Debug	50 25 12.5	— — —	ns ns ns
J4	TCLK rise and fall times	—	3	ns

Table continues on the next page...

Table 13. JTAG full voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
J5	Boundary scan input data setup time to TCLK rise	20	—	ns
J6	Boundary scan input data hold time after TCLK rise	0	—	ns
J7	TCLK low to boundary scan output data valid	—	25	ns
J8	TCLK low to boundary scan output high-Z	—	25	ns
J9	TMS, TDI input data setup time to TCLK rise	8	—	ns
J10	TMS, TDI input data hold time after TCLK rise	1.4	—	ns
J11	TCLK low to TDO data valid	—	22.1	ns
J12	TCLK low to TDO high-Z	—	22.1	ns
J13	TRST assert time	100	—	ns
J14	TRST setup time (negation) to TCLK high	8	—	ns

**Figure 6. Test clock input timing****Figure 7. Boundary scan (JTAG) timing**

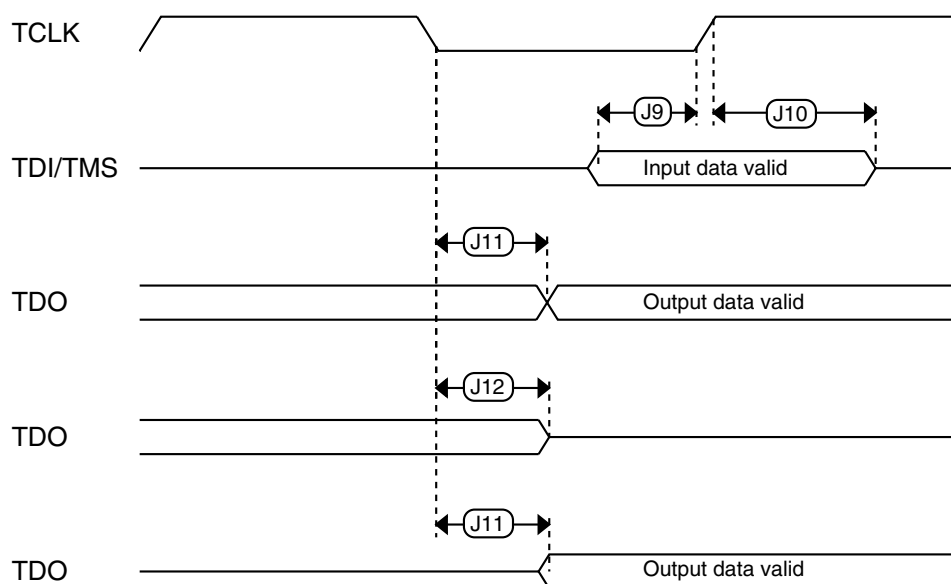


Figure 8. Test Access Port timing

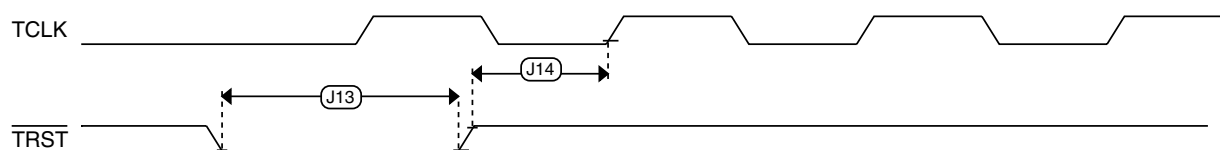


Figure 9. $\overline{\text{TRST}}$ timing

6.2 System modules

There are no specifications necessary for the device's system modules.

6.3 Clock modules

Table 14. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
J_{cyc_fll}	FLL period jitter $f_{VCO} = 48 \text{ MHz}$ $f_{VCO} = 98 \text{ MHz}$	—	180	—	ps	
$t_{fll_acquire}$	FLL target frequency acquisition time	—	—	1	ms	6
PLL						
f_{vco}	VCO operating frequency	48.0	—	100	MHz	
I_{pll}	PLL operating current PLL @ 96 MHz ($f_{osc_hi_1} = 8 \text{ MHz}$, $f_{pll_ref} = 2 \text{ MHz}$, VDIV multiplier = 48)	—	1060	—	μA	7
I_{pll}	PLL operating current PLL @ 48 MHz ($f_{osc_hi_1} = 8 \text{ MHz}$, $f_{pll_ref} = 2 \text{ MHz}$, VDIV multiplier = 24)	—	600	—	μA	7
f_{pll_ref}	PLL reference frequency range	2.0	—	4.0	MHz	
J_{cyc_pll}	PLL period jitter (RMS) $f_{vco} = 48 \text{ MHz}$ $f_{vco} = 100 \text{ MHz}$	—	120	—	ps	8
J_{acc_pll}	PLL accumulated jitter over 1 μs (RMS) $f_{vco} = 48 \text{ MHz}$ $f_{vco} = 100 \text{ MHz}$	—	1350	—	ps	8
D_{lock}	Lock entry frequency tolerance	± 1.49	—	± 2.98	%	
D_{unl}	Lock exit frequency tolerance	± 4.47	—	± 5.97	%	
t_{pll_lock}	Lock detector detection time	—	—	$150 \times 10^{-6} + 1075(1/f_{pll_ref})$	s	9

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=0.
3. The resulting system clock frequencies should not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature should be considered.
4. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32=1.
5. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
6. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.
7. Excludes any oscillator currents that are also consuming power while PLL is in operation.
8. This specification was obtained using a Freescale developed PCB. PLL jitter is dependent on the noise characteristics of each PCB and results will vary.
9. This specification applies to any time the PLL VCO divider or reference divider is changed, or changing from PLL disabled (BLPE, BLPI) to PLL enabled (PBE, PEE). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

6.3.2 Oscillator electrical specifications

This section provides the electrical characteristics of the module.

Table 20. Flash command timing specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
t_{swapx01}	Swap Control execution time	—	200	—	μs	
t_{swapx02}	• control code 0x02	—	70	150	μs	
t_{swapx04}	• control code 0x04	—	70	150	μs	
t_{swapx08}	• control code 0x08	—	—	30	μs	
$t_{\text{pgmpart32k}}$	Program Partition for EEPROM execution time • 32 KB FlexNVM	—	70	—	ms	
t_{setramff}	Set FlexRAM Function execution time: • Control Code 0xFF	—	50	—	μs	
t_{setram8k}	• 8 KB EEPROM backup	—	0.3	0.5	ms	
$t_{\text{setram32k}}$	• 32 KB EEPROM backup	—	0.7	1.0	ms	
Byte-write to FlexRAM for EEPROM operation						
$t_{\text{eewr8bers}}$	Byte-write to erased FlexRAM location execution time	—	175	260	μs	3
t_{eewr8b8k}	Byte-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{eewr8b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{eewr8b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Word-write to FlexRAM for EEPROM operation						
$t_{\text{eewr16bers}}$	Word-write to erased FlexRAM location execution time	—	175	260	μs	
$t_{\text{eewr16b8k}}$	Word-write to FlexRAM execution time: • 8 KB EEPROM backup	—	340	1700	μs	
$t_{\text{eewr16b16k}}$	• 16 KB EEPROM backup	—	385	1800	μs	
$t_{\text{eewr16b32k}}$	• 32 KB EEPROM backup	—	475	2000	μs	
Longword-write to FlexRAM for EEPROM operation						
$t_{\text{eewr32bers}}$	Longword-write to erased FlexRAM location execution time	—	360	540	μs	
$t_{\text{eewr32b8k}}$	Longword-write to FlexRAM execution time: • 8 KB EEPROM backup	—	545	1950	μs	
$t_{\text{eewr32b16k}}$	• 16 KB EEPROM backup	—	630	2050	μs	
$t_{\text{eewr32b32k}}$	• 32 KB EEPROM backup	—	810	2250	μs	

1. Assumes 25 MHz flash clock frequency.

2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3. For byte-writes to an erased FlexRAM location, the aligned word containing the byte must be erased.

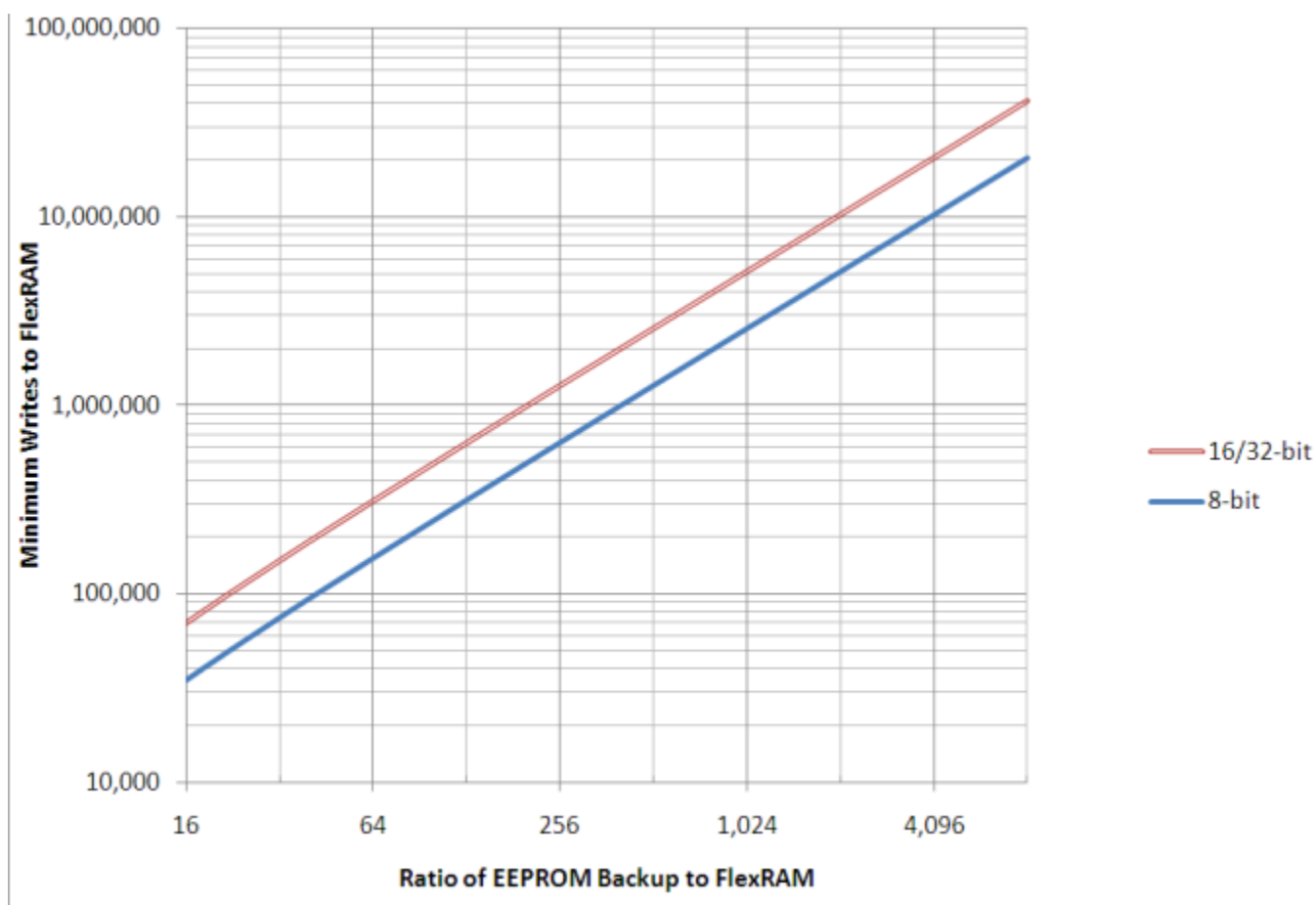


Figure 10. EEPROM backup writes to FlexRAM

6.4.2 EzPort Switching Specifications

Table 23. EzPort switching specifications

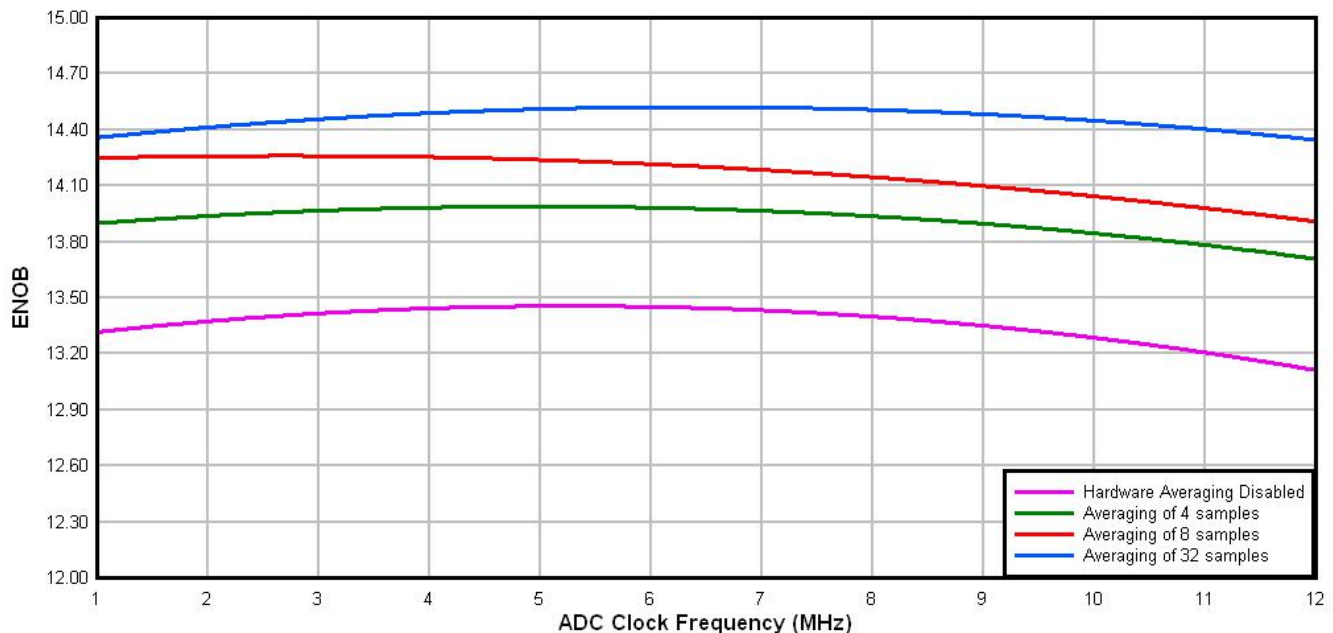
Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
EP1	EZP_CK frequency of operation (all commands except READ)	—	$f_{SYS}/2$	MHz
EP1a	EZP_CK frequency of operation (READ command)	—	$f_{SYS}/8$	MHz
EP2	EZP_CS negation to next EZP_CS assertion	$2 \times t_{EZP_CK}$	—	ns
EP3	EZP_CS input valid to EZP_CK high (setup)	5	—	ns
EP4	EZP_CK high to EZP_CS input invalid (hold)	5	—	ns
EP5	EZP_D input valid to EZP_CK high (setup)	2	—	ns
EP6	EZP_CK high to EZP_D input invalid (hold)	5	—	ns
EP7	EZP_CK low to EZP_Q output valid	—	16	ns
EP8	EZP_CK low to EZP_Q output invalid (hold)	0	—	ns
EP9	EZP_CS negation to EZP_Q tri-state	—	12	ns

Table 27. 16-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Symbol	Description	Conditions ¹	Min.	Typ. ²	Max.	Unit	Notes
E_{IL}	Input leakage error			$I_{IN} \times R_{AS}$		mV	I_{IN} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	—	1.715	—	mV/°C	
V_{TEMP25}	Temp sensor voltage	25 °C	—	719	—	mV	

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume $V_{DDA} = 3.0$ V, Temp = 25°C, $f_{ADCK} = 2.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and the ADLPC bit (low power). For lowest power operation the ADLPC bit must be set, the HSC bit must be clear with 1 MHz ADC conversion clock speed.
4. $1 \text{ LSB} = (V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. Input data is 100 Hz sine wave. ADC conversion clock < 12 MHz.
7. Input data is 1 kHz sine wave. ADC conversion clock < 12 MHz.

Typical ADC 16-bit Differential ENOB vs ADC Clock
100Hz, 90% FS Sine Input

**Figure 15. Typical ENOB vs. ADC_CLK for 16-bit differential mode**

6.6.3.2 12-bit DAC operating behaviors

Table 32. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	150	μA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	700	μA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	μs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	μs	1
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	μs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFFF	$V_{DACR} - 100$	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	± 8	LSB	2
DNL	Differential non-linearity error — $V_{DACR} > 2$ V	—	—	± 1	LSB	3
DNL	Differential non-linearity error — $V_{DACR} = V_{REF_OUT}$	—	—	± 1	LSB	4
V_{OFFSET}	Offset error	—	± 0.4	± 0.8	%FSR	5
E_G	Gain error	—	± 0.1	± 0.6	%FSR	5
PSRR	Power supply rejection ratio, $V_{DDA} \geq 2.4$ V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	$\mu V/C$	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
R_{op}	Output resistance load = 3 k Ω	—	—	250	Ω	
SR	Slew rate -80h → F7Fh → 80h - High power (SP_{HP}) - Low power (SP_{LP})	1.2 0.05	1.7 0.12	— —	V/ μs	
CT	Channel to channel cross talk	—	—	-80	dB	
BW	3dB bandwidth - High power (SP_{HP}) - Low power (SP_{LP})	550 40	— —	— —	kHz	

1. Settling within ± 1 LSB
2. The INL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
3. The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV
4. The DNL is measured for 0 + 100 mV to $V_{DACR} - 100$ mV with $V_{DDA} > 2.4$ V
5. Calculated by a best fit curve from $V_{SS} + 100$ mV to $V_{DACR} - 100$ mV
6. $V_{DDA} = 3.0$ V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

Table 34. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1915	1.195	1.1977	V	
V_{out}	Voltage reference output — factory trim	1.1584	—	1.2376	V	
V_{out}	Voltage reference output — user trim	1.193	—	1.197	V	
V_{step}	Voltage reference trim step	—	0.5	—	mV	
V_{tdrift}	Temperature drift ($V_{max} - V_{min}$ across the full temperature range)	—	—	80	mV	
I_{bg}	Bandgap only current	—	—	80	μA	1
I_{lp}	Low-power buffer current	—	—	360	μA	1
I_{hp}	High-power buffer current	—	—	1	mA	1
ΔV_{LOAD}	Load regulation • current = ± 1.0 mA	—	200	—	μV	1, 2
T_{stup}	Buffer startup time	—	—	100	μs	
V_{vdift}	Voltage drift ($V_{max} - V_{min}$ across the full voltage range)	—	2	—	mV	1

1. See the chip's Reference Manual for the appropriate settings of the VREF Status and Control register.
2. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 35. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	$^{\circ}C$	

Table 36. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	

6.7 Timers

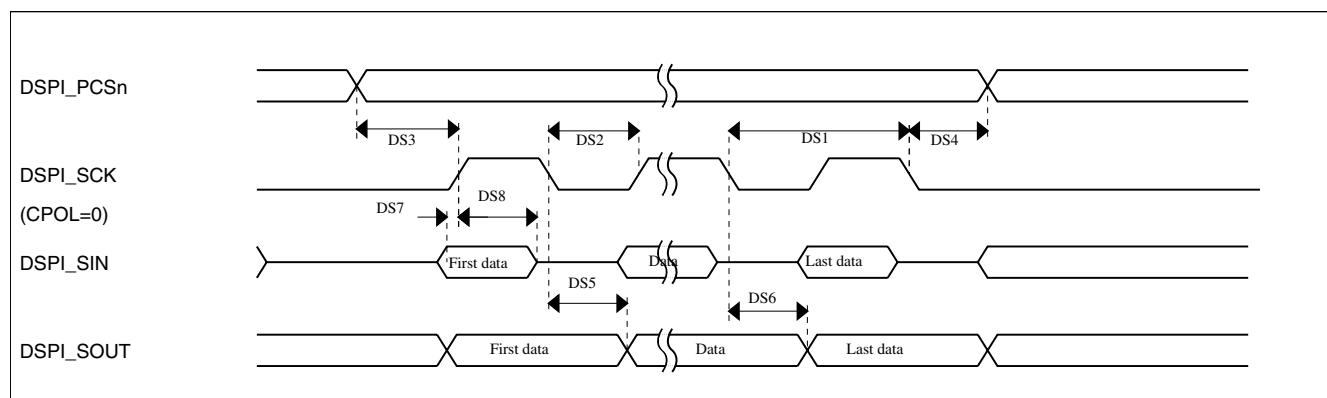
See [General switching specifications](#).

6.8 Communication interfaces

Table 39. Master mode DSPI timing (full voltage range) (continued)

Num	Description	Min.	Max.	Unit	Notes
DS2	DSPI_SCK output high/low time	$(t_{\text{SCK}/2}) - 4$	$(t_{\text{SCK}/2}) + 4$	ns	
DS3	DSPI_PCSn valid to DSPI_SCK delay	$(t_{\text{BUS}} \times 2) - 4$	—	ns	2
DS4	DSPI_SCK to DSPI_PCSn invalid delay	$(t_{\text{BUS}} \times 2) - 4$	—	ns	3
DS5	DSPI_SCK to DSPI_SOUT valid	—	10	ns	
DS6	DSPI_SCK to DSPI_SOUT invalid	-4.5	—	ns	
DS7	DSPI_SIN to DSPI_SCK input setup	20.5	—	ns	
DS8	DSPI_SCK to DSPI_SIN input hold	0	—	ns	

1. The DSPI module can operate across the entire operating voltage for the processor, but to run across the full voltage range the maximum frequency of operation is reduced.
2. The delay is programmable in SPIx_CTARn[PSSCK] and SPIx_CTARn[CSSCK].
3. The delay is programmable in SPIx_CTARn[PASC] and SPIx_CTARn[ASC].

**Figure 23. DSPI classic SPI timing — master mode****Table 40. Slave mode DSPI timing (full voltage range)**

Num	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
	Frequency of operation	—	6.25	MHz
DS9	DSPI_SCK input cycle time	$8 \times t_{\text{BUS}}$	—	ns
DS10	DSPI_SCK input high/low time	$(t_{\text{SCK}/2}) - 4$	$(t_{\text{SCK}/2}) + 4$	ns
DS11	DSPI_SCK to DSPI_SOUT valid	—	20	ns
DS12	DSPI_SCK to DSPI_SOUT invalid	0	—	ns
DS13	DSPI_SIN to DSPI_SCK input setup	2	—	ns
DS14	DSPI_SCK to DSPI_SIN input hold	7	—	ns
DS15	DSPI_SS active to DSPI_SOUT driven	—	19	ns
DS16	DSPI_SS inactive to DSPI_SOUT not driven	—	19	ns

Pinout

121 MAP BGA	100 LQFP	Pin Name	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
J2	17	ADC1_DM1	ADC1_DM1	ADC1_DM1								
K1	18	PGA0_DP/ ADC0_DP0/ ADC1_DP3	PGA0_DP/ ADC0_DP0/ ADC1_DP3	PGA0_DP/ ADC0_DP0/ ADC1_DP3								
K2	19	PGA0_DM/ ADC0_DM0/ ADC1_DM3	PGA0_DM/ ADC0_DM0/ ADC1_DM3	PGA0_DM/ ADC0_DM0/ ADC1_DM3								
L1	20	PGA1_DP/ ADC1_DP0/ ADC0_DP3	PGA1_DP/ ADC1_DP0/ ADC0_DP3	PGA1_DP/ ADC1_DP0/ ADC0_DP3								
L2	21	PGA1_DM/ ADC1_DM0/ ADC0_DM3	PGA1_DM/ ADC1_DM0/ ADC0_DM3	PGA1_DM/ ADC1_DM0/ ADC0_DM3								
F5	22	VDDA	VDDA	VDDA								
G5	23	VREFH	VREFH	VREFH								
G6	24	VREFL	VREFL	VREFL								
F6	25	VSSA	VSSA	VSSA								
L3	26	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18	VREF_OUT/ CMP1_IN5/ CMP0_IN5/ ADC1_SE18								
K5	27	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23	DAC0_OUT/ CMP1_IN3/ ADC0_SE23								
L7	—	RTC_ WAKEUP_B	RTC_ WAKEUP_B	RTC_ WAKEUP_B								
L4	28	XTAL32	XTAL32	XTAL32								
L5	29	EXTAL32	EXTAL32	EXTAL32								
K6	30	VBAT	VBAT	VBAT								
H5	31	PTE24	ADC0_SE17	ADC0_SE17	PTE24		UART4_TX			EWM_OUT_b		
J5	32	PTE25	ADC0_SE18	ADC0_SE18	PTE25		UART4_RX			EWM_IN		
H6	33	PTE26	DISABLED		PTE26		UART4_CTS_ b			RTC_CLKOUT		
J6	34	PTA0	JTAG_TCLK/ SWD_CLK/ EZP_CLK	TSIO_CH1	PTA0	UART0_CTS_ b/ UART0_COL_ b	FTM0_CH5				JTAG_TCLK/ SWD_CLK	EZP_CLK
H8	35	PTA1	JTAG_TDI/ EZP_DI	TSIO_CH2	PTA1	UART0_RX	FTM0_CH6				JTAG_TDI	EZP_DI
J7	36	PTA2	JTAG_TDO/ TRACE_SWO/ EZP_DO	TSIO_CH3	PTA2	UART0_TX	FTM0_CH7				JTAG_TDO/ TRACE_SWO	EZP_DO
H9	37	PTA3	JTAG_TMS/ SWD_DIO	TSIO_CH4	PTA3	UART0_RTS_ b	FTM0_CH0				JTAG_TMS/ SWD_DIO	
J8	38	PTA4/ LLWU_P3	NMI_b/ EZP_CS_b	TSIO_CH5	PTA4/ LLWU_P3		FTM0_CH1				NMI_b	EZP_CS_b

8.2 K10 Pinouts

The below figure shows the pinout diagram for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see the previous section.